Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting Information

High-performance CdScInO thin-film transistors and their stability improvement under negative bias (illumination) temperature stress

Teng Long,‡[a] Xingqiang Dai,‡[a] Linfeng Lan,*[a,] Caihao Deng,[a] Zhuo Chen,[a] Changchun He,[b] Lu Liu,[b] Xiaobao Yang,[b] and Junbiao Peng[a]

[a]State Key Laboratory of Luminescent Materials and Devices, South China University of Technology, Guangzhou, China. E-mail: lanlinfeng@scut.edu.cn

[b]School of Physics Science and Technology, South China University of Technology, Guangzhou, China

‡Contributed equally to this work.

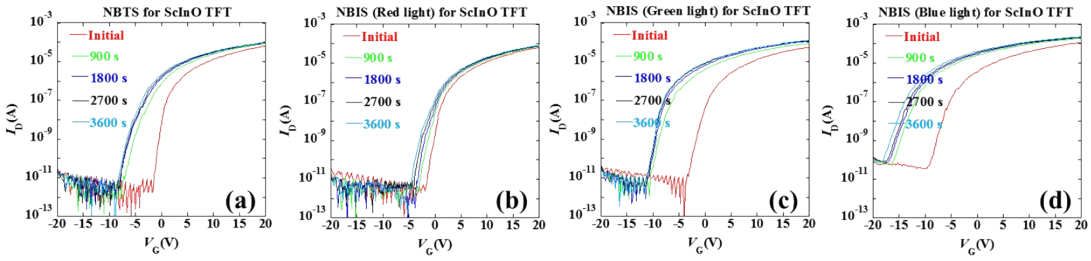

Figure S1. NBI/TS stability of the ScInO TFTs. (a) NBTS at 80 °C; (b) NBIS under 650 nm red light illumination; (c) NBIS under 550 nm green light illumination; (d) NBIS under 450 nm blue light illumination.

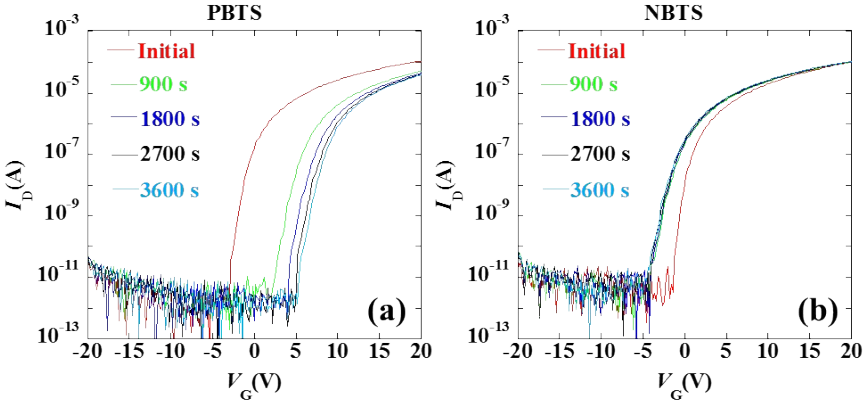

Figure S2. (a) PBTS and (b) NBTS stability at 80 °C

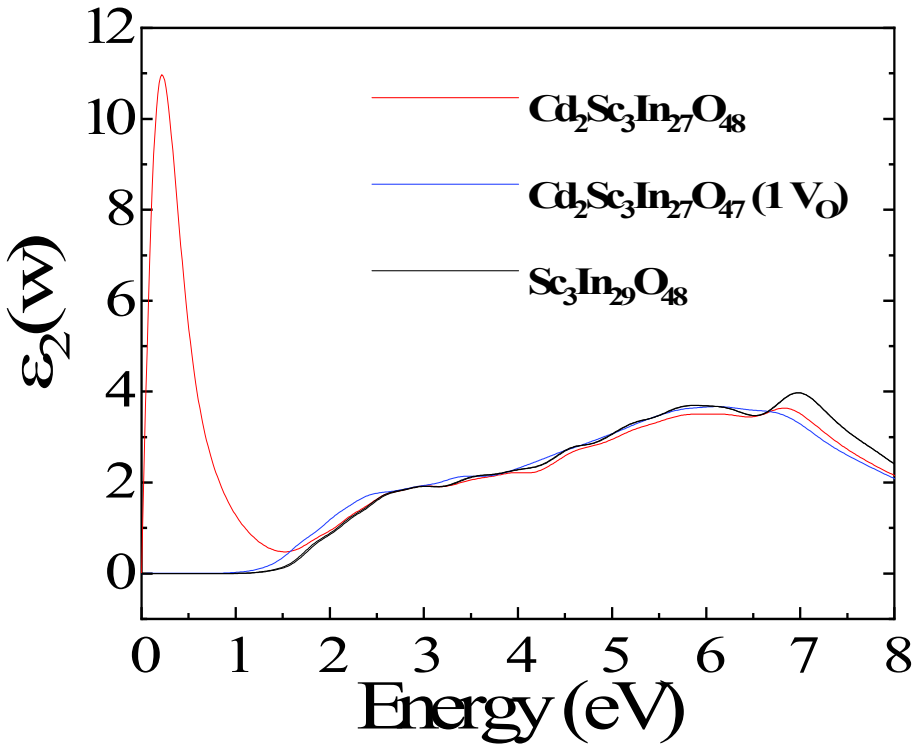

Figure S3. The calculated ε_2 for $Sc_3In_{29}O_{48}$, $Cd_2Sc_3In_{27}O_{48}$, and $Cd_2Sc_3In_{27}O_{47}$ with 1 V_O.